

#### **Features**

- Trench Power LV MOSFET Technology
- High Density Cell Design for Ultra Low RDS(on)
- ESD Protected Up to 2KV(HBM)
- · Exceptional On-Resistance and Maximum DC Current Capability
- · Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- Halogen Free."Green"Device (Note1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

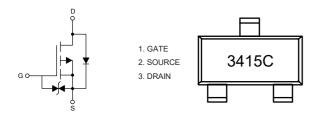
## **Maximum Ratings**

- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 120°C/W Junction to Ambient

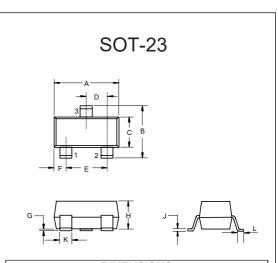
Parameter	Symbol	Rating	Unit		
Drain-Source Voltage		V <sub>DS</sub>	-20	V	
Gate-Source Volltage		V <sub>GS</sub> ±10		V	
Continuous Drain Current	T <sub>A=</sub> 25 °C	· I <sub>D</sub>	-3.9	Α	
	T <sub>A=</sub> 100 °C		-2.4		
Pulsed Drain Current		I <sub>DM</sub>	-16	Α	
Total Power Dissipation		P <sub>D</sub>	1	W	

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

## **Internal Structure and Marking Code**

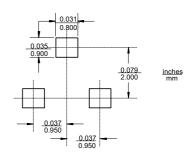


# P-CHANNEL MOSFET



DIMENSIONS					
DIM INCH		HES MM		М	NOTE
MII	MIN	MAX	MIN	MAX	NOTE
Α	0.110	0.120	2.80	3.04	
В	0.083	0.104	2.10	2.64	
С	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
Н	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

## Suggested Solder Pad Layout





# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

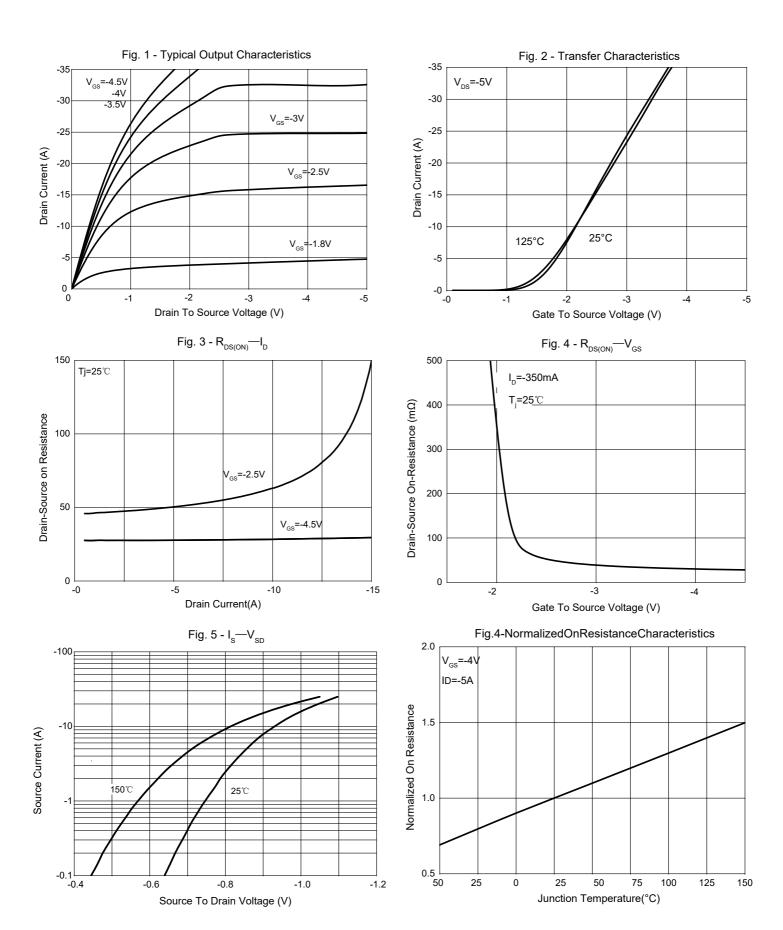
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics						1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-20			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	•	
		V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, T <sub>J</sub> =150 °C			-100	μA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±10	uA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.55	-0.85	-1.25	V	
Drain-Source On-Resistance		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A		28	40		
	R <sub>DS(on)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4A		50	75	$m\Omega$	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-2A		150	200		
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-5A		-0.9	-1.2	V	
Body-Diode Continuous Current	I <sub>S</sub>				-0.83	Α	
Gate resistance	R <sub>G</sub>	f=1MHz, Open drain		16		Ω	
Dynamic Characteristics <sup>(Note 3</sup>	3)						
Input Capacitance	C <sub>iss</sub>			540			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =-10V, $V_{GS}$ =0V,f =1MHz		120		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			100			
Switching Characteristics (Note	: 3)						
Total Gate Charge	Qg			13			
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =-10V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-5A		2		nC	
Gate-Drain Charge	$Q_{gd}$			2			
Turn-On Delay Time	t <sub>d(on)</sub>			5			
Turn-On Rise Time	t <sub>r</sub>	V <sub>GS</sub> =-10V,V <sub>DD</sub> =-10V,I <sub>D</sub> =-5A,		47		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_{GEN}$ =2.2 $\Omega$		52			
Turn-Off Fall Time	t <sub>f</sub>			69			
Reverse Recovery Charge	Q <sub>rr</sub>	I - 50 4/4-4000/		2.5		nC	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-5A,d <sub>i</sub> /d <sub>t</sub> =100A/us		20		ns	

Note: 2. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.

<sup>3.</sup> Guaranteed by Design, Not Subject to Production Testing.

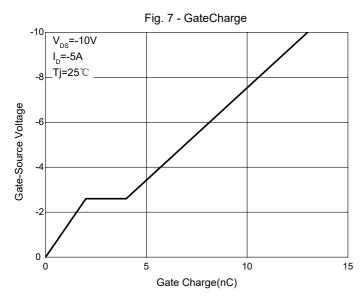


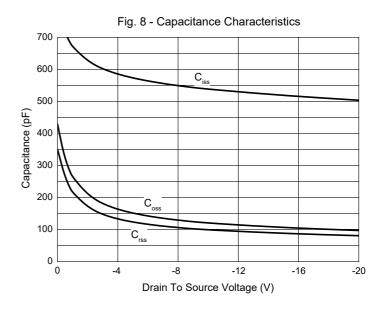
### **Curve Characteristics**

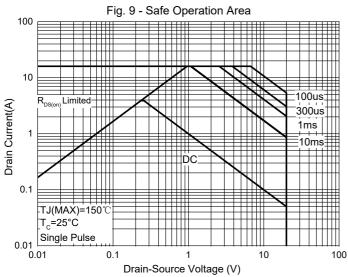


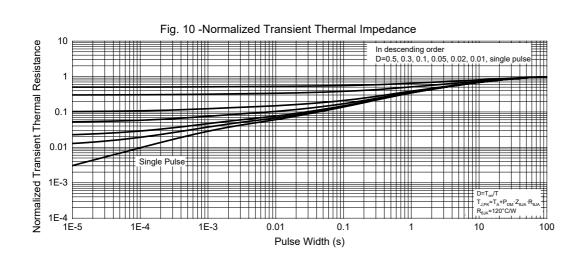


### **Curve Characteristics**











## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

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